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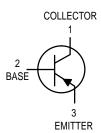
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# **Amplifier Transistors PNP Silicon**



## **MAXIMUM RATINGS**

Rating	Symbol	BC 556	BC 557	BC 558	Unit
Collector-Emitter Voltage	VCEO	-65	-45	-30	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-80	-50	-30	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0			Vdc
Collector Current — Continuous	IC	-100			mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0			mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12		Watt mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150			°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -2.0 mAdc, I <sub>B</sub> = 0)	BC556 BC557 BC558	V(BR)CEO	-65 -45 -30	_ _ _	_ _ _	V	
Collector-Base Breakdown Voltage (I <sub>C</sub> = -100 μAdc)	BC556 BC557 BC558	V(BR)CBO	-80 -50 -30	_ _ _ _	_ _ _	V	
Emitter – Base Breakdown Voltage (I <sub>E</sub> = –100 μAdc, I <sub>C</sub> = 0)	BC556 BC557 BC558	V(BR)EBO	-5.0 -5.0 -5.0	_ _ _	_ _ _	V	
Collector–Emitter Leakage Current (VCES = -40 V) (VCES = -20 V)  (VCES = -20 V, T <sub>A</sub> = 125°C)	BC556 BC557 BC558 BC556 BC557 BC558	I <sub>CES</sub>		-2.0 -2.0 -2.0 - -	-100 -100 -100 -4.0 -4.0 -4.0	nA μA	





## BC556,B BC557A,B,C BC558B

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$  unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (I <sub>C</sub> = $-10 \mu Adc$ , V <sub>CE</sub> = $-5.0 V$ ) (I <sub>C</sub> = $-2.0 \mu Adc$ , V <sub>CE</sub> = $-5.0 V$ )	BC557A BC556B/557B/558B BC557C BC556 BC557 BC558	hFE		90 150 270 — —	  500 800 800	_
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	BC557A BC556B/557B/558B BC557C BC557A BC556B/557B/558B BC557C		120 180 420 — — —	170 290 500 120 180 300	220 460 800 — — —	
Collector-Emitter Saturation Voltage (IC = -10 mAdc, IB = -0.5 mAdc) (IC = -10 mAdc, IB = see Note 1) (IC = -100 mAdc, IB = -5.0 mAdc)		VCE(sat)	_ _ _	-0.075 -0.3 -0.25	-0.3 -0.6 -0.65	<b>V</b>
Base-Emitter Saturation Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -0.5 mAdc) (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc)		V <sub>BE</sub> (sat)	_ _	-0.7 -1.0	_ _	V
Base–Emitter On Voltage (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc) (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc)		VBE(on)	-0.55 	-0.62 -0.7	-0.7 -0.82	V
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain — Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 V, f = 100 MHz)	BC556 BC557 BC558	fΤ	_ _ _	280 320 360		MHz
Output Capacitance (V <sub>CB</sub> = -10 V, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	_	3.0	6.0	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ V, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, $\Delta$ f = $200$ Hz)	BC556 BC557 BC558	NF	_ _ _	2.0 2.0 2.0	10 10 10	dB
Small–Signal Current Gain (IC = -2.0 mAdc, VCE = -5.0 V, f = 1.0 kHz)	BC556 BC557/558 BC557A BC556B/557B/558B BC557C	h <sub>fe</sub>	125 125 125 125 240 450		500 900 260 500 900	

Note 1:  $I_C = -10$  mAdc on the constant base current characteristics, which yields the point  $I_C = -11$  mAdc,  $V_{CE} = -1.0$  V.

### BC557/BC558

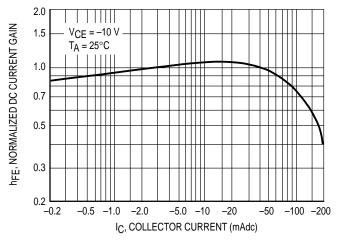


Figure 1. Normalized DC Current Gain

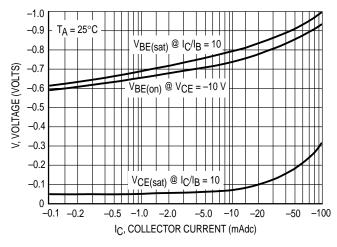


Figure 2. "Saturation" and "On" Voltages

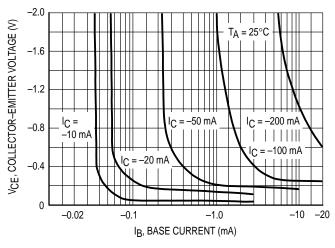


Figure 3. Collector Saturation Region

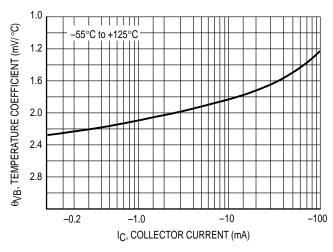


Figure 4. Base-Emitter Temperature Coefficient

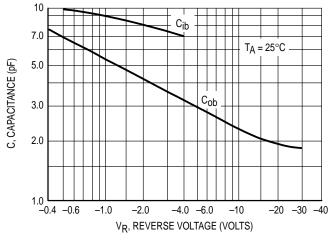


Figure 5. Capacitances

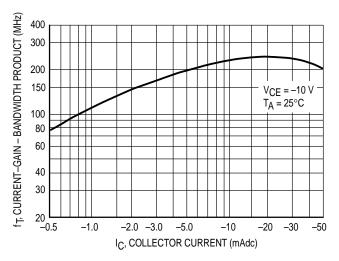


Figure 6. Current-Gain - Bandwidth Product

## **BC556**

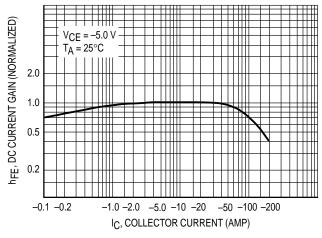


Figure 7. DC Current Gain

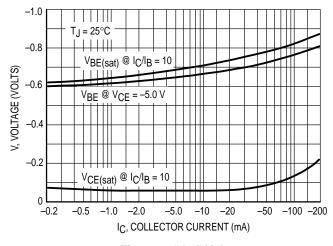


Figure 8. "On" Voltage

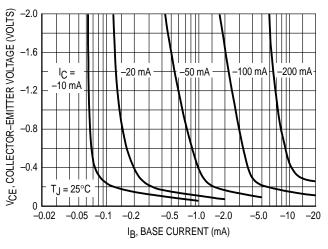


Figure 9. Collector Saturation Region

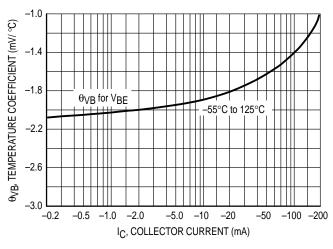


Figure 10. Base-Emitter Temperature Coefficient

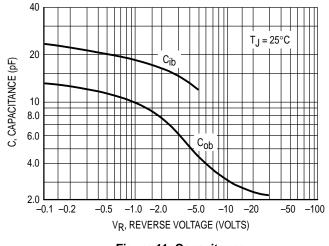


Figure 11. Capacitance

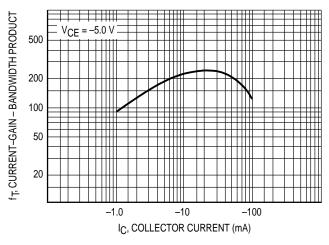


Figure 12. Current-Gain - Bandwidth Product

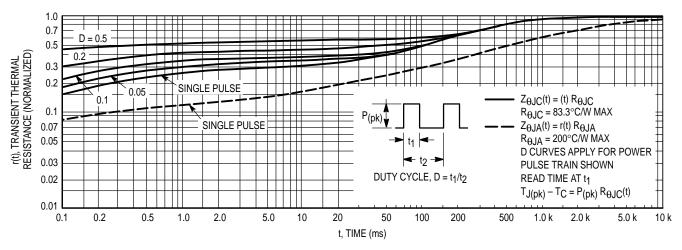


Figure 13. Thermal Response

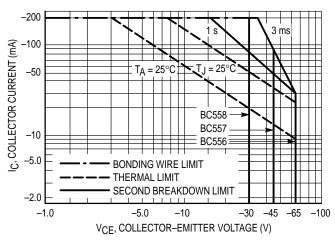
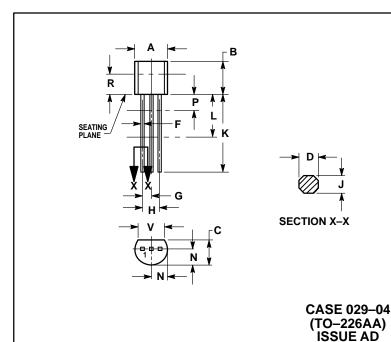


Figure 14. Active Region — Safe Operating Area

The safe operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100	_	2.54	
R	0.115		2.93		
V	0.135		3 43		

STYLE 17: PIN 1. COLLECTOR

- 3. EMITTER

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